

**IN THE SPECIFICATION:**

Please change the title to:

Fabrication Of Ultra Shallow Junctions From A Solid Source With Fluorine  
Implantation

**IN THE CLAIMS:**

Please enter the following clean version of amend Claim 4:

A' SUB B.7 4. The method of claim 1, wherein after heating 90% of that portion of the dopant  
that has diffused into the semiconductor substrate is located within about 50 nm from  
the surface of the semiconductor substrate.